

Patent Abstracts of Japan

PUBLICATION NUMBER : 2000012539
PUBLICATION DATE : 14-01-00

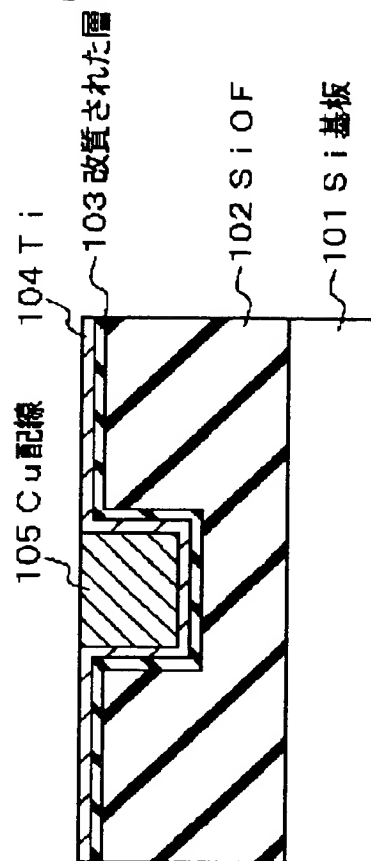
APPLICATION DATE : 17-06-98
APPLICATION NUMBER : 10169778

APPLICANT : NEC CORP;

INVENTOR : KOYANAGI KENICHI;

INT.CL. : H01L 21/3205 H01L 21/316

TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : **PROBLEM TO BE SOLVED:** To enable avoidance of deterioration of an adhesion between an interlayer insulating film and a barrier metal or wiring layer, when a wiring groove is made in a silicon oxide film containing fluorine as the interlayer insulating film and the wiring layer is formed in the groove through a barrier metal of Ti, etc.

SOLUTION The manufacturing method includes steps of forming an SiO₂ film 102 on a substrate 101, forming an opening for wiring formation in the SiO₂ film, removing fluorine contained in the SiO₂ film from a surface of the opening, subjecting the fluorine-removed surface of the opening to an oxygen plasma process, and providing wiring metals 104 and 105 to the opening.

COPYRIGHT (C)2000,JPO